

**SWITCHING
N-CHANNEL POWER MOS FET
INDUSTRIAL USE**

DESCRIPTION

The 2SK1293 is N-channel MOS Field Effect Transistor designed for solenoid, motor and lamp driver.

FEATURES

- Low On-state Resistance
 $R_{DS(on)} \leq 0.08 \Omega$ ($V_{GS} = 10 V, I_D = 15 A$)
 $R_{DS(on)} \leq 0.1 \Omega$ ($V_{GS} = 4 V, I_D = 15 A$)
- Low C_{iss} $C_{iss} = 2\ 200$ pF TYP.
- Built-in G-S Gate Protection Diodes

QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

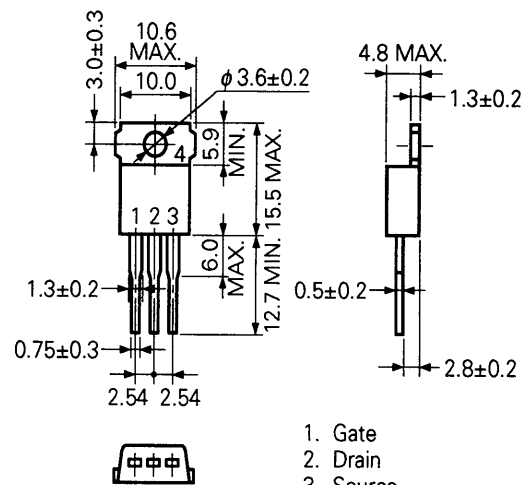
ABSOLUTE MAXIMUM RATINGS ($T_a = 25 \text{ }^\circ\text{C}$)

Drain to Source Voltage	V_{DSS}	100	V
Gate to Source Voltage	$V_{GSS(AC)}$	± 20	V
Drain Current (DC)	$I_{D(DC)}$	± 30	A
Drain Current (pulse)	$I_{D(pulse)^*}$	± 120	A
Total Power Dissipation ($T_a = 25 \text{ }^\circ\text{C}$)	P_{T1}	1.5	W
Total Power Dissipation ($T_c = 25 \text{ }^\circ\text{C}$)	P_{T2}	75	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

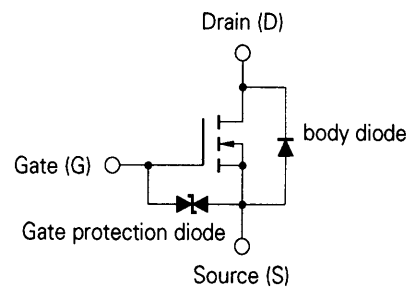
* $PW \leq 10 \mu s$, Duty Cycle $\leq 1 \%$

PACKAGE DIMENSIONS

(in millimeters)



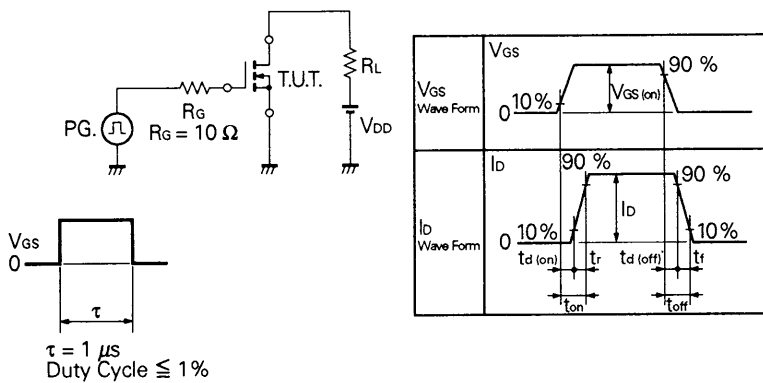
1. Gate
2. Drain
3. Source
4. Fin (Drain)



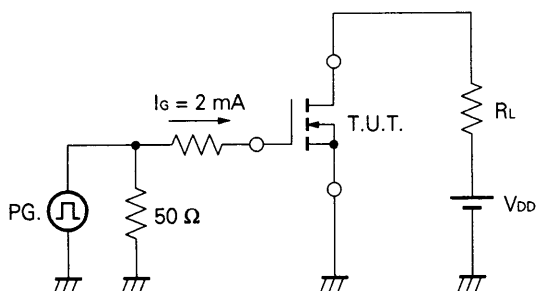
ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-state Resistance	R _{DS(on)}		0.07	0.08	Ω	V _{GS} = 10 V, I _D = 15 A
Drain to Source On-state Resistance	R _{DS(on)}		0.08	0.1	Ω	V _{GS} = 4.0 V, I _D = 15 A
Gate to Source Cutoff Voltage	V _{GS(off)}	1.0		2.5	V	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance	y _{fs}	12			S	V _{DS} = 10 V, I _D = 15 A
Drain Leakage Current	I _{DSS}			10	μA	V _{DS} = 100 V, V _{GS} = 0
Gate to Source Leakage Current	I _{GSS}			±10	μA	V _{GS} = ±20 V, V _{DS} = 0
Input Capacitance	C _{iss}		2 200		pF	V _{DS} = 10 V V _{GS} = 0 f = 1 MHz
Output Capacitance	C _{oss}		550		pF	
Reverse Transfer Capacitance	C _{rss}		90		pF	
Turn-On Delay Time	t _{d(on)}		25		ns	V _{GS(on)} = 10 V V _{DD} = 50 V I _D = 15 A, R _G = 10 Ω R _L = 3.3 Ω
Rise Time	t _r		160		ns	
Turn-Off Delay Time	t _{d(off)}		200		ns	
Fall Time	t _f		150		ns	
Total Gate Charge	Q _G		50		nC	V _{GS} = 10 V I _D = 30 A V _{DD} = 80 V
Gate to Source Charge	Q _{GS}		10		nC	
Gate to Drain Charge	Q _{GD}		10		nC	
Diode Forward Voltage	V _{SD}		1.2		V	I _{SD} = 30 A, V _{GS} = 0
Reverse Recovery Time	t _{rr}		200		ns	I _F = 30 A, V _{GS} = 0
Reverse Recovery Charge	Q _{rr}		550		nC	di/dt = 50 A/μs

Test Circuit 1: Switching Time

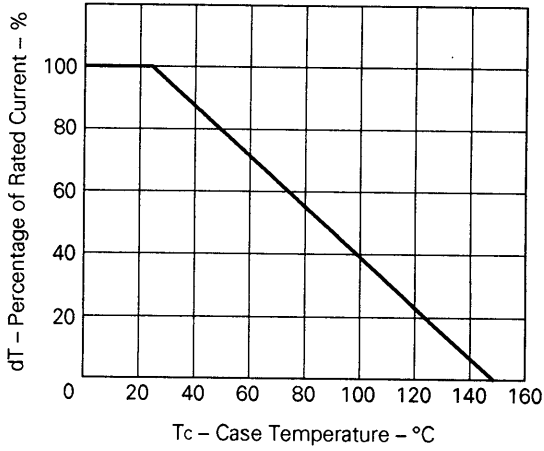


Test Circuit 2: Gate Charge

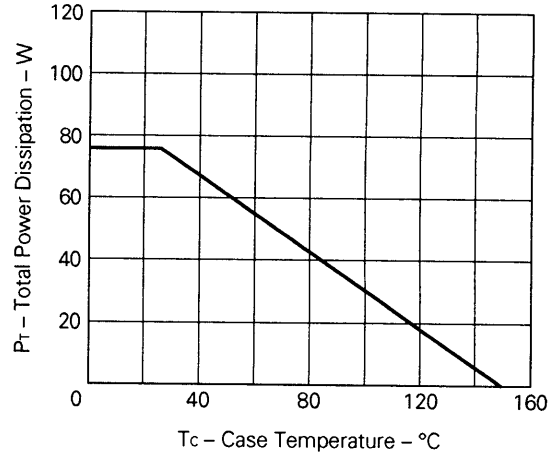


TYPICAL CHARACTERISTICS (T_a = 25 °C)

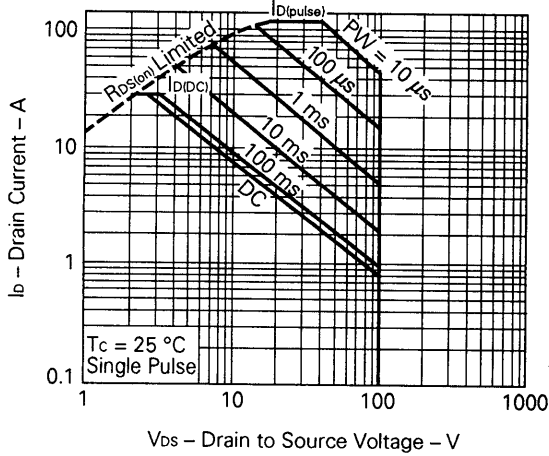
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



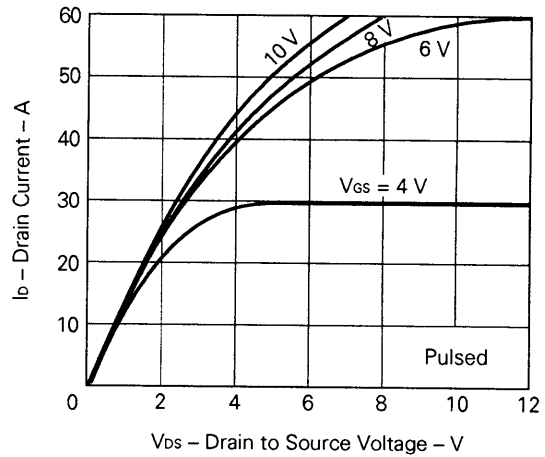
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



FORWARD BIAS SAFE OPERATING AREA



DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



TRANSFER CHARACTERISTICS

